WPH4003

ON Semiconductor®

N-Channel Power MOSFET 1700V, 3A, 10.5Ω, TO-3PF-3L

http://onsemi.com

Features

- ON-resistance RDS (on) = 8.2Ω (typ.)
- 10V drive
- Input Capacitance Ciss=850pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1700	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only maximum temperature Tch=150°C	3	А
Drain Current (DC)	I _{Dpack*2}	Tc=25°C (Our ideal heat dissipation condition) *3	2.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	6	А
Allerrable Derree Dissinskies	D-		3.0	W
Allowable Power Dissipation PD		Tc=25°C	55	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		49	mJ
Avalanche Current *5	IAV		3	А

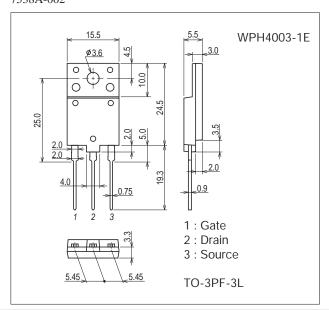
Note:*1 Shows chip capability

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7538A-002



Product & Package Information

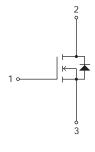
Package : TO-3PF-3LJEITA, JEDEC : SC-96

• Minimum Packing Quantity: 30 pcs./magazine

Marking

Electrical Connection





^{*2} Package limited

^{*3} Our condition is radiation from backside.

^{*4} VDD=50V, L=10mH, IAV=3A (Fig.1)

^{*5} L≤10mH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Cymphal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	1700			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1360V, V _{GS} =0V			1	mA	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2		4	V	
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1.5A	1.2	2.4		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =1.5A, V _G S=10V		8.2	10.5	Ω	
Input Capacitance	Ciss			850		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		90		pF	
Reverse Transfer Capacitance	Crss			27		pF	
Turn-ON Delay Time	t _d (on)			19		ns	
Rise Time	t _r	Con Fig 2		21		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		200		ns	
Fall Time	tf			55		ns	
Total Gate Charge	Qg			48		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =3A		6		nC	
Gate-to-Drain "Miller" Charge	Qgd			22		nC	
Diode Forward Voltage	V _{SD}	IS=3A, VGS=0V		0.8	1.5	V	
Reverse Recovery Time	t _{rr}	See Fig.3		410		ns	
Reverse Recovery Charge	Q _{rr}	IS=3A, VGS=0V, di/dt=100A/μs		3000		nC	

Fig.1 Unclamped Inductive Switching Test Circuit

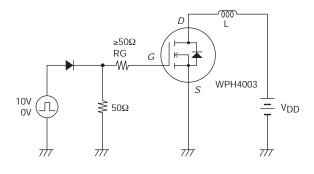


Fig.2 Switching Time Test Circuit

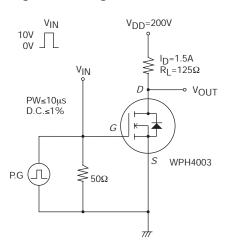
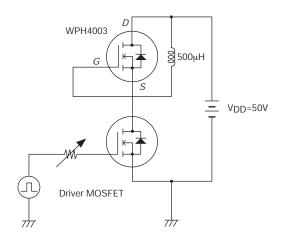
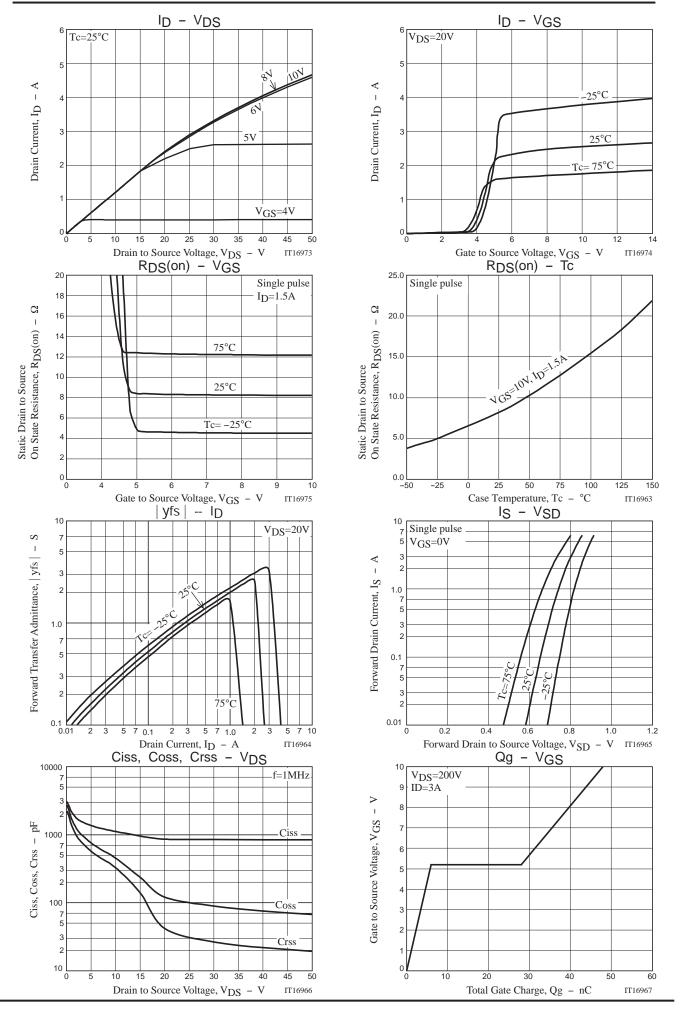


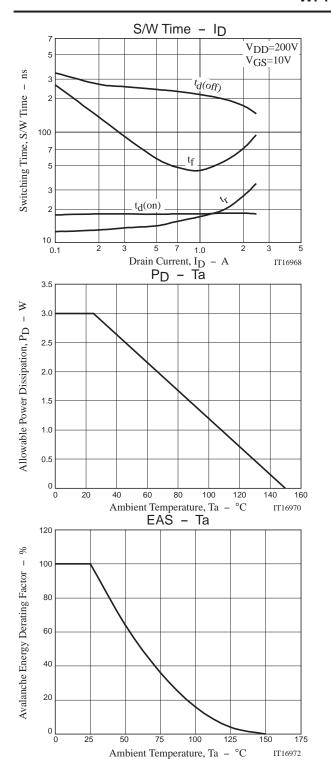
Fig.3 Reverse Recovery Time Test Circuit

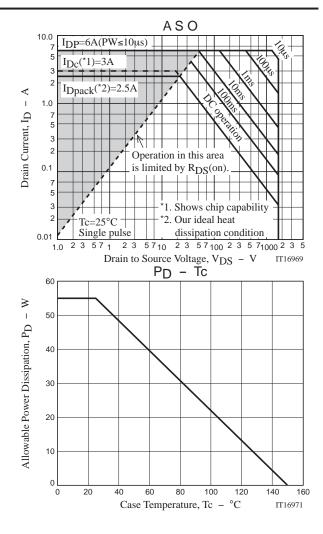


Ordering Information

Device	Package	Shipping	memo	
WPH4003-1E	TO-3PF-3L	30pcs./magazine	Pb Free	





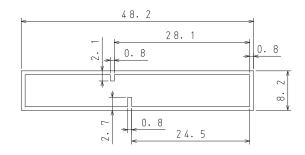


Magazine Specification

WPH4003-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format		
I donago iyamo	Magazine	Inner box	Outer box	Inner BOX	Outer BOX	
TO-3PF-3L	30	360	1440	SPD-0V0001 12 magazines contained Dimensions:mm(external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178	



Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

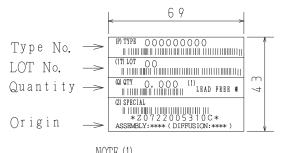
3. Storage method to magazine

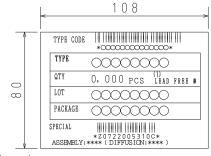


4. Inner box label (unit:mm)



It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



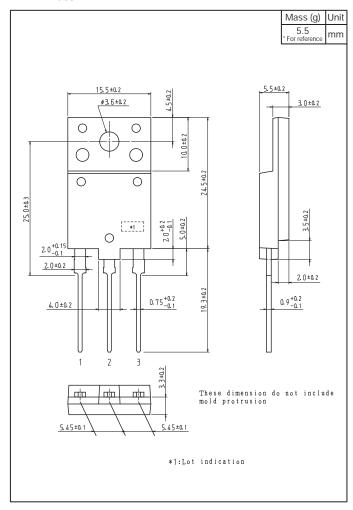


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase			
LEAD FRE	E 3	JEITA Phase 3A			

Outline Drawing

WPH4003-1E



Note on usage: Since the WPH4003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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